**Product data sheet** 

## 1. General description

Dual Silicon Carbide Schottky diodes in a TO3PF plastic package, designed for high frequency switched-mode power supplies.





### 2. Features and benefits

- · Highly stable switching performance
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant
- Insulated package rated at 2500V RMS

## 3. Applications

- · Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage			6	50		V
I <sub>O(AV)</sub>	average forward current	$\delta$ = 0.5 ; square-wave pulse; T <sub>h</sub> ≤ 51 °C; both diodes conducting; Fig. 1; Fig. 2; Fig. 3	<u>3</u>		А		
T <sub>j</sub>	junction temperature		175		°C		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	$I_F = 10 \text{ A}; T_j = 25 ^{\circ}\text{C}; \text{ per diode}; Fig. 5$		-	1.5	1.7	V
		$I_F = 10 \text{ A}; T_j = 150 ^{\circ}\text{C}; \text{ per diode}; Fig. 5$		-	1.8	2.2	V
Dynamic	characteristics					•	•
Q <sub>r</sub>	recovered charge	$I_F = 10 \text{ A}$ ; $dI_F/dt = 500 \text{ A/}\mu\text{s}$ ; $V_R = 400 \text{ V}$ ; $T_j = 25 ^{\circ}\text{C}$ ; per diode; Fig. 7		-	14	-	nC

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode	mb O O O	
2	K	cathode	<sub>⊚</sub> O <sub>⊚</sub>	A1
3	A2	anode		K
mb	n.c.	mounting base; isolated		sym125

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package	Orderable part number	Packing	Small packing	Package	Package
	name		method	quantity	version	issue date
WNSC2D20650CJ	TO3PF	WNSC2D20650CJQ	Tube	30	SOT1293	16-Mar-2006

# 7. Marking

### Table 4. Marking codes

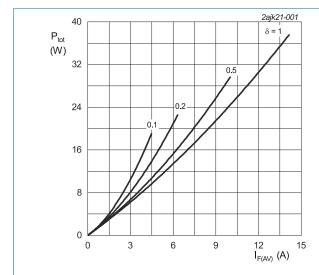
Type number	Marking codes
WNSC2D20650CJ	WNSC2D 20650CJ

# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		650	V
$V_{\text{RWM}}$	crest working reverse voltage		650	V
$V_R$	reverse voltage	DC	650	V
I <sub>O(AV)</sub>	average forward current	$δ$ = 0.5; square-wave pulse; $T_h \le 51$ °C; both diodes conducting; Fig. 1; Fig. 2; Fig. 3	20	А
I <sub>FRM</sub>	repetitive peak forward current	$δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_h \le 89 °C$ ; square-wave pulse; per diode	20	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	50	А
		$t_p$ = 10 $\mu$ s; $T_{j(init)}$ = 25 °C; square-wave pulse; per diode	450	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	sine-wave pulse; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 10 \text{ ms}$	12.5	A <sup>2</sup> s
T <sub>stg</sub>	storage temperature		-55 to 175	°C
T <sub>j</sub>	junction temperature		175	°C



$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_o &= 1.916 \text{ V}; \text{ R}_s = 0.0523 \text{ }\Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode

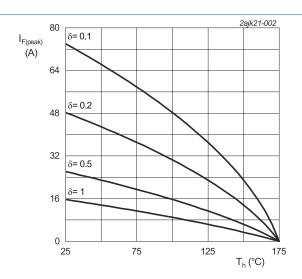


Fig. 2. Current derating as a function of heatsink temperature; per diode

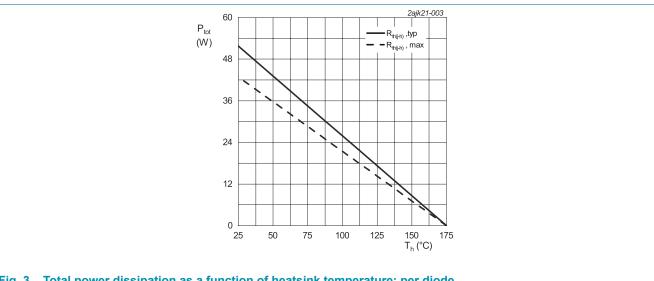
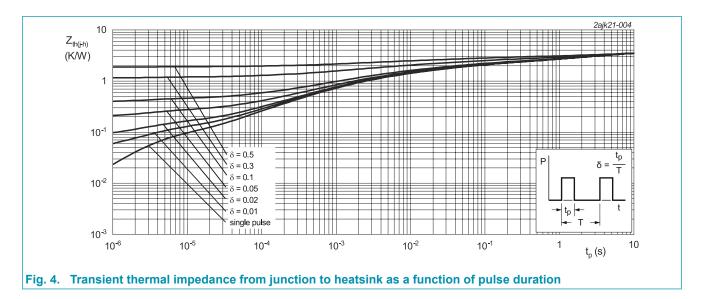


Fig. 3. Total power dissipation as a function of heatsink temperature; per diode

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to	with heatsink compound; per diode; Fig. 4	-	-	3.5	K/W
	heatsink	with heatsink compound; both diodes conducting	-	-	2.7	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	35	-	K/W



### 10. Isolation characteristics

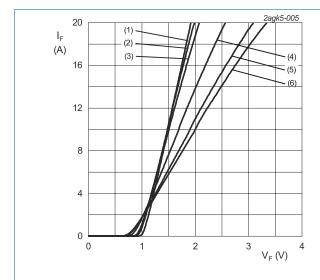
**Table 7. Isolation characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	f = 1 MHz; from cathode to external heatsink	-	10	-	pF

### 11. Characteristics

**Table 8. Characteristics** 

Symbol	Parameter	Conditions	Mir	Тур	Max	Unit
Static cha	aracteristics					
$V_{F}$	forward current	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 5</u>	-	1.5	1.7	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; per diode; <u>Fig. 5</u>	-	1.8	2.2	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 175 °C; per diode; <u>Fig. 5</u>	-	2	2.3	V
I <sub>R</sub>	reverse current	$V_R = 650 \text{ V}; T_j = 25 ^{\circ}\text{C}; \text{ per diode}; Fig. 6$	-	0.5	50	μA
		V <sub>R</sub> = 650 V; T <sub>j</sub> = 175 °C; per diode; <u>Fig. 6</u>	-	25	250	μA
Dynamic	characteristics			'		
Q <sub>r</sub>	recovered charge	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; per diode; Fig. 7$	-	14	-	nC
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 1 V; T <sub>j</sub> = 25 °C	-	310	-	pF
		f = 1 MHz; V <sub>R</sub> = 300 V; T <sub>j</sub> = 25 °C	-	36	-	pF
		f = 1 MHz; V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	32	-	pF
E <sub>as</sub>	non-repetitive avalanche energy	$I_R$ = 5.5 A; L = 5 mH; $T_{j(init)}$ = 25 °C; per diode	75	-	-	mJ



 $V_o = 1.916 \text{ V}; R_s = 0.0523 \Omega$ 

(1)  $T_j = -55$  °C; typical values

(2)  $T_j = 0$  °C; typical values (3)  $T_j = 25$  °C; typical values

(4) T<sub>i</sub> = 100 °C; typical values

(5) T<sub>i</sub> = 150 °C; typical values

(6) T<sub>i</sub> = 175 °C; typical values Fig. 5. Forward current as a function of forward voltage; typical values; per diode

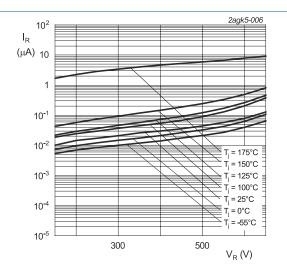
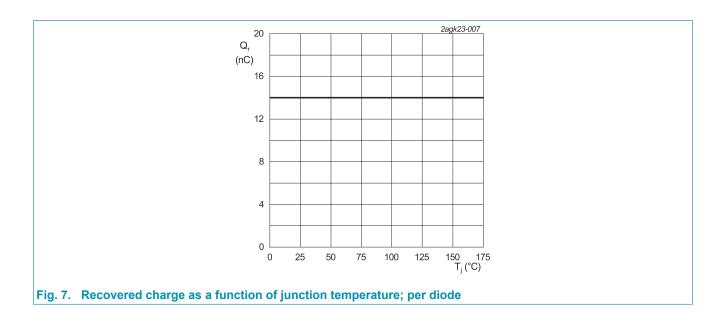
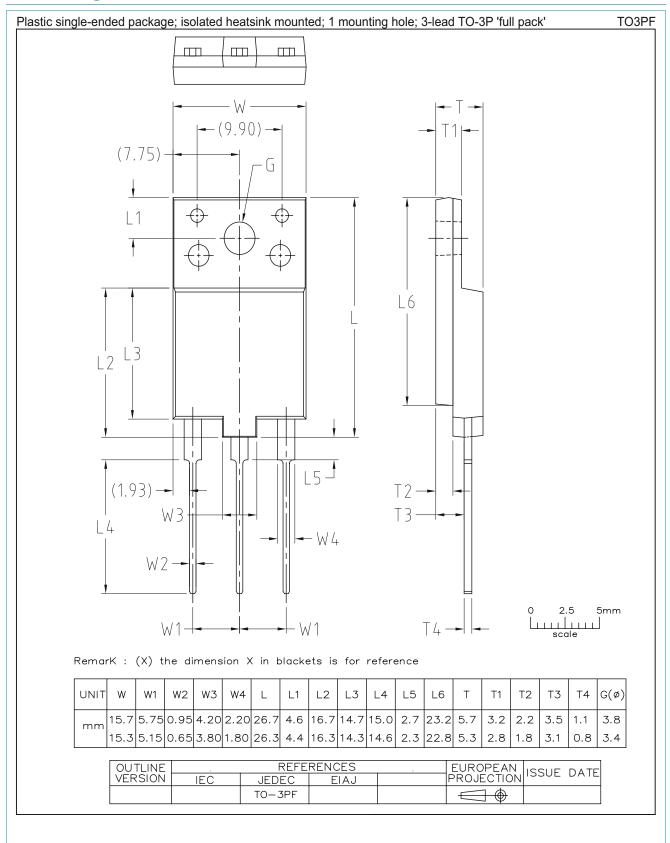


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value; per diode



# 12. Package outline



## 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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